PLASMA PROCESSING APPARATUS AND PLASMA PROCESSING METHOD

ABSTRACT

A technique increases a deposition rate of a precoat. A plasma processing apparatus includes a chamber, a gas supply, a substrate support in the chamber, a plasma generator that generates a plasma in the chamber, and a controller. The controller performs control operations including (a) supplying a first processing gas from the gas supply to the chamber. The first processing gas includes an alkyne gas having three or more carbon atoms. The operations include (b) generating, with the plasma generator, a plasma from the first processing gas and forming a precoat including a carbon-containing film on a component in the chamber, (c) providing a substrate on the substrate support, (d) supplying a second processing gas from the gas supply to the chamber, and (e) generating, with the plasma generator, a plasma from the second processing gas and performing plasma processing of the substrate.

Fig. 3